

UNISONIC TECHNOLOGIES CO., LTD

UTT2N10 Preliminary Power MOSFET

100V COMPLEMENTARY ENHANCEMENT MODE MOSFET (N-CHANNEL)

■ DESCRIPTION

The UTC **UTT2N10** is a complementary enhancement mode MOSFET, it uses UTC advanced technology to provide customers low on resistance, low gate charge and low threshold voltage.

The UTC **UTT2N10** is universally applied in DC-AC Inverters and DC Motor control.

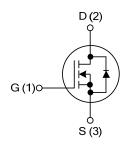
■ FEATURES

* N-CHANNEL

 $R_{DS(on)} < 0.7\Omega \text{ @V}_{GS} = 10V$ $R_{DS(on)} < 1.0\Omega \text{ @V}_{GS} = 4.5V$

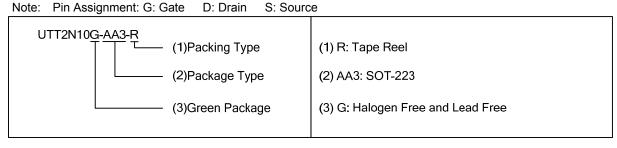
* High switching speed

■ SYMBOL



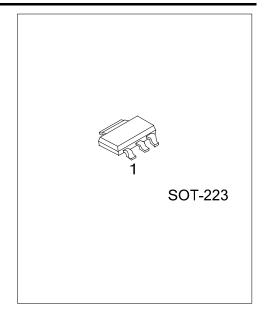


| Ordering Number | Package | Pin Assignment | | | Doolsing | |
|-----------------|---------|----------------|---|---|-----------|--|
| | | 1 | 2 | 3 | Packing | |
| UTT2N10G-AA3-R | SOT-223 | G | D | S | Tape Reel | |



■ MARKING





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■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT | |
|--|------------|---|-----------------|-------|---|
| Gate-Source Voltage | | V_{GSS} | ±20 | V | |
| Drain-Source Voltage | | V_{DSS} | 100 | V | |
| Drain Current | Continuous | V _{GS} =10V, T _A =25°C, t ≤10 sec | I _D | 1 | Α |
| | Pulsed | V _{GS} =10V, T _A =25°C (Note1) | I _{DM} | 4.3 | Α |
| Power Dissipation $ \frac{T_A=25^{\circ}C}{Derating} $ | | 0 | 0.87 | W | |
| | | P _D | 6.94 | mW/°C | |
| Junction Temperature | | TJ | -55~+150 | °C | |
| Storage Temperature Range | | T _{STG} | -55~+150 | °C | |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

| PARAMETER | SYMBOL | RATINGS | UNIT |
|----------------------------|---------------|---------|------|
| Junction to Ambient (Note) | θ_{JA} | 55 | °C/W |
| Junction to Case | θις | 12 | °C/W |

Notes: θ_{JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.

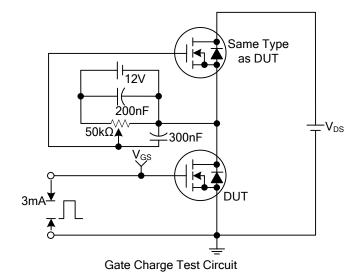
■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

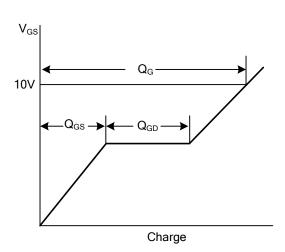
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT | |
|---|----------------------------|-----------------------------|---|-----|------|------|------|--|
| OFF CHARACTERISTICS | | | | | | | | |
| Drain-Source Breakdown Voltage | | BV _{DSS} | I _D =250μA, V _{GS} =0V | 100 | | | V | |
| Drain-Source Leakage Current | | I _{DSS} | V _{DS} =100V, V _{GS} =0V | | | 0.5 | μΑ | |
| Gate-Source Leakage Current | Forward | I _{GSS} | V _{GS} =+20V, V _{DS} =0V | | | +100 | nA | |
| | Reverse | | V _{GS} =-20V, V _{DS} =0V | | | -100 | nΑ | |
| ON CHARACTERISTICS | | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | $V_{DS}=V_{GS}$, $I_D=250\mu A$ | 2 | | 4 | V | |
| Static Drain-Source On-State Resistance(Note 1) | | R _{DS(ON)} | V _{GS} =10V, I _D =1.5A | | | 0.7 | Ω | |
| | | | V _{GS} =4.5V, I _D =1A | | | 1.0 | Ω | |
| DYNAMIC PARAMETERS | | | | | | | | |
| Input Capacitance (Note 3) | out Capacitance (Note 3) | | | | 220 | | pF | |
| Output Capacitance (Note 3) | | Coss | V_{GS} =0V, V_{DS} =25V, f=1.0MHz | | 33 | | pF | |
| Reverse Transfer Capacitance (Note 3) | | C_{RSS} | | | 17 | | pF | |
| SWITCHING PARAMETERS | | | | | | | | |
| Total Gate Charge (Note 3) | | Q_G | | | 21 | | nC | |
| Gate to Source Charge (Note 3) | | Q_GS | V_{GS} =10V, V_{DS} =50V, I_{D} =1A | | 2 | | nC | |
| Gate to Drain Charge (Note 3) | e to Drain Charge (Note 3) | | | | 1.5 | | nC | |
| Turn-ON Delay Time (Note 2, 3) | | t _{D(ON} | | | 25.6 | | ns | |
| Rise Time (Note 2, 3) | | t_R | V _{DD} =30V, I _D =1A, R _G ≈6Ω, | | 16 | | ns | |
| Turn-OFF Delay Time (Note 2, 3) | | t _{D(OFF)} | V _{GS} =10V | | 55 | | ns | |
| Fall-Time (Note 2, 3) | | $t_{\scriptscriptstyle{F}}$ | | | 13 | | ns | |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | | | |
| Maximum Body-Diode Continuous Current | | Is | T _A =25°C (Note 2) | | | 1 | Α | |
| Maximum Body-Diode Pulsed Current | | I _{SM} | T _A =25°C (Note 3) | | | 4.3 | Α | |
| Drain-Source Diode Forward Voltage (Note 1) | | V_{SD} | I _S =1.5A, V _{GS} =0V | | | 0.95 | ٧ | |

Notes: 1. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%

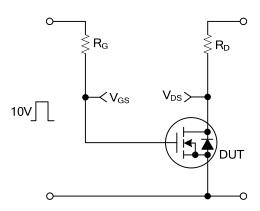
- 2. Switching characteristics are independent of operating junction temperature
- 3. For design aid only, not subject to production testing

■ TEST CIRCUITS AND WAVEFORMS

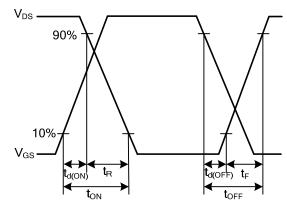




Gate Charge Waveforms







Resistive Switching Waveforms

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